

Low VF Schottky Diode Array

- Reverse voltage: 40 V
- Forward current: 0.2 A
- Small diode quad array for polarity independance, reverse polarity protection and low loss bridge rectification
- Very low forward voltage: 0.55 @ 0.1 A (per diode)
- Fast switching
- Pb-free (ROHS compliant) package
- Qualified according AEC Q101



BAS4002A-RPP



Туре	Package	Configuration	Marking
BAS4002A-RPP	SOT143	bridge	E9s

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage ¹⁾	V _R	40	V	
Peak reverse voltage ¹⁾	V _{RM}	40		
RMS reverse voltage ¹⁾	V _{R(RMS)}	28		
Forward current ¹⁾ , $T_{S} \le 124 \text{ °C}$	I _F	200	mA	
Non-repetitive peak surge forward current	/ _{FSM}	2	A	
(<i>t</i> ≤ 10 ms)				
Junction temperature	Ti	150	°C	
Storage temperature	T _{stq}	-65150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 130	K/W

¹For $T_A > 25^{\circ}$ C the derating of V_R and I_F has to be considered.

 $^2 \rm For}$ calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance





Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current ¹⁾ (per diode)	I _R				μA
V _R = 30 V		-	-	2	
V _R = 40 V		-	-	10	
Forward voltage ^{1) 2)} (per diode)	V _F				V
/ _F = 10 mA		-	0.39	0.44	
/ _F = 60 mA		-	0.49	0.55	
/ _F = 100 mA		-	0.55	0.62	
<i>I</i> _F = 200 mA		-	0.69	0.79	
AC Characteristics	1		1		
Diode capacitance (per diode)	CT	-	2	5	pF
V _R = 5 V, <i>f</i> = 1 MHz					

Electrical Characteristics at T_{Δ} = 25°C, unless otherwise specified

¹Pulsed test, $t_p = 300 \ \mu s$; D = 0.01

²When used as shown for Reverse Polarity Protection (RPP, see page 4), the voltage available to the circuit being protected will be two diode drops below the power supply voltage. In other words, the supply current will pass through two diodes.



Diode capacitance $C_T = f(V_R)$

f = 1MHz (per diode)



Reverse current $I_R = f(T_A)$

 $V_{\rm R}$ = Parameter (per diode)



Reverse current $I_{R} = f(V_{R})$ T_{A} = Parameter (per diode)



Forward Voltage $V_F = f(T_A)$ I_F = Parameter (per diode)





Forward current $I_{F} = f(V_{F})$

(per diode)



Forward current $I_{\rm F}$ = $f(T_{\rm S})$

BAS4002-RPP

Application example BAS4002A-RPP

Advanced Reverse Polarity Protection(RPP): due to diode orientation, circuit at the right will be protected from damage and will also function normally in the event reverse polarity is applied to pins 2 and 3 of the BAS4002A-RPP.









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